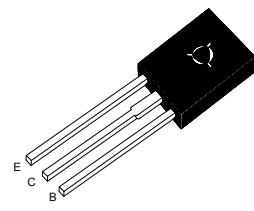


2SB772T-HAF

PNP Silicon Epitaxial Power Transistor

These devices are intended for use in audio frequency power amplifier and low speed switching applications



TO-126 Plastic Package

Features

- Halogen and Antimony Free(HAF), RoHS compliant

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	40	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	30	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current - DC	$-I_C$	3	A
Collector Current - Pulse ¹⁾	$-I_{\text{CP}}$	7	A
Base Current - DC	$-I_B$	0.6	A
Total Power Dissipation	P_{tot}	10 1	W
Operating and Storage Junction Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

¹⁾ PW = 10 ms, Duty Cycle $\leq 50\%$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{\text{CE}} = 2\text{ V}$, $-I_C = 20\text{ mA}$ at $-V_{\text{CE}} = 2\text{ V}$, $-I_C = 1\text{ A}$	h_{FE}	30	-	-	-
	h_{FE}	60	-	120	-
	h_{FE}	100	-	200	-
	h_{FE}	160	-	320	-
	h_{FE}	200	-	400	-
Collector Base Cutoff Current at $-V_{\text{CB}} = 30\text{ V}$	$-I_{\text{CBO}}$	-	-	1	μA
Emitter Base Cutoff Current at $-V_{\text{EB}} = 3\text{ V}$	$-I_{\text{EBO}}$	-	-	1	μA
Collector Base Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(\text{BR})\text{CBO}}$	40	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(\text{BR})\text{CEO}}$	30	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 1\text{ mA}$	$-V_{(\text{BR})\text{EBO}}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 2\text{ A}$, $-I_B = 200\text{ mA}$	$-V_{\text{CE}(\text{sat})}$	-	-	0.5	V
Base Emitter Saturation Voltage at $-I_C = 2\text{ A}$, $-I_B = 200\text{ mA}$	$-V_{\text{BE}(\text{sat})}$	-	-	2	V
Emitter Output Capacitance at $-V_{\text{CB}} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	55	-	pF
Current Gain Bandwidth Product at $-I_C = 100\text{ mA}$, $-V_{\text{CE}} = 5\text{ V}$	f_T	-	80	-	MHz

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ISO14001 : 2004 ISO 9001 : 2008 OHSAS 18001 : 2007 IECQ QC 080000
Certificate No. 121505007 Certificate No. 50114012 Certificate No. 0513150006 Certificate No. ESD MM001

Dated : 05/08/2016 Rev:01

2SB772T-HAF

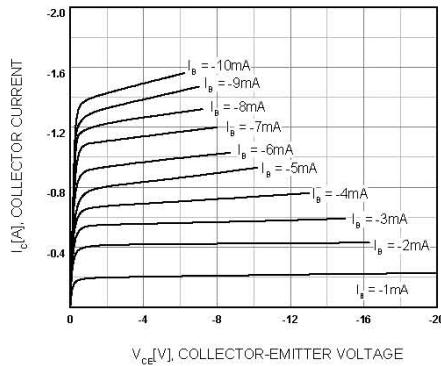


Figure 1. Static Characteristic

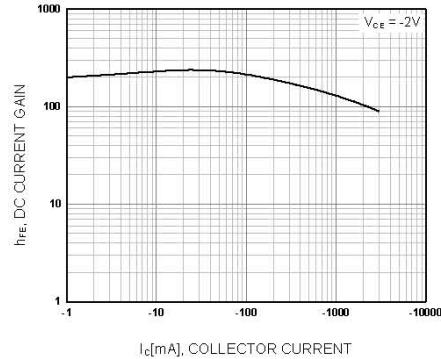
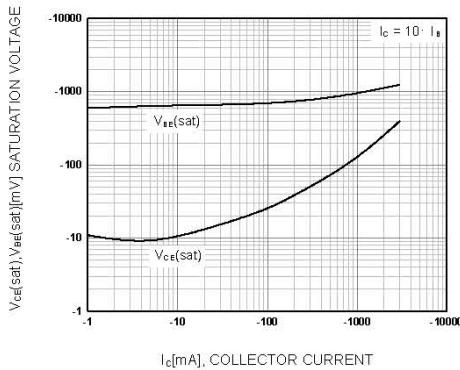


Figure 2. DC current Gain



**Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**

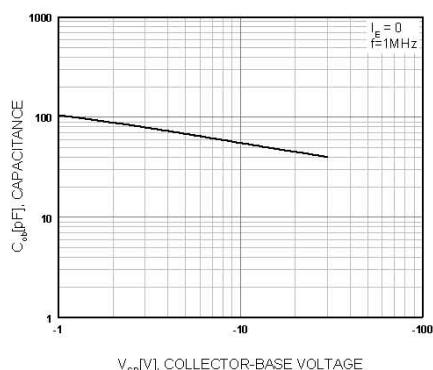


Figure 4. Collector Output Capacitance

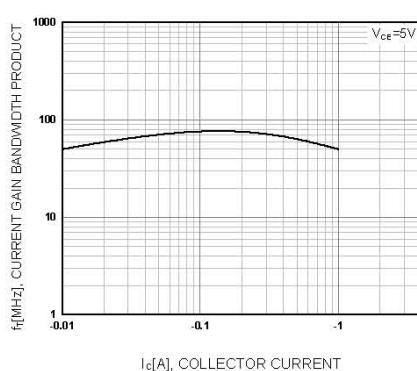


Figure 5. Current Gain Bandwidth Product

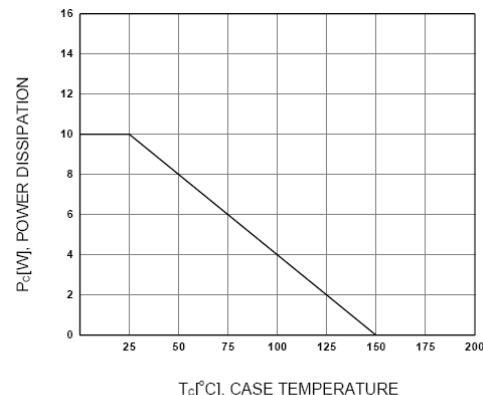


Figure 6 Power Derating

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